



#### **General Description**

The WSK140N08 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

#### **Product Summery**

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
80V	4.8mΩ	140A

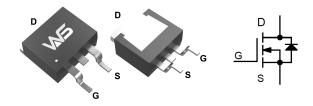
#### **Applications**

Power Management for Inverter Systems.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

#### **TO-263-2L Pin Configuration**



#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit		
Common	Ratings (T <sub>c</sub> =25°C Unless Otherwise Noted)			•	
$V_{DSS}$	Drain-Source Voltage	80	V		
$V_{GSS}$	Gate-Source Voltage	±25			
T <sub>J</sub>	Maximum Junction Temperature	175	°C		
T <sub>STG</sub>	Storage Temperature Range		-55 to 175	°C	
I <sub>S</sub>	Diode Continuous Forward Current	T <sub>C</sub> =25°C	140	А	
Mounted	on Large Heat Sink				
I <sub>DM</sub>	Pulsed Drain Current *	T <sub>C</sub> =25°C	551**	А	
l <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> =25°C	140	A	
		T <sub>C</sub> =100°C	91		
P <sub>D</sub>	Maximum Dayyar Dissination	T <sub>C</sub> =25°C	250	W	
	Maximum Power Dissipation	T <sub>C</sub> =100°C	125		
$R_{\theta JC}$	Thermal Resistance-Junction to Case		0.61	90/4/	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	- °C/W		
Avalanch	e Ratings			•	
E <sub>AS</sub>	Avalanche Energy, Single Pulsed	L=0.5mH	762***	mJ	

Note: \* Repetitive rating; pulse width limited by junction temperatur

<sup>\*\*</sup> Drain current is limited by junction temperature

<sup>\*\*\*</sup> VD=64V



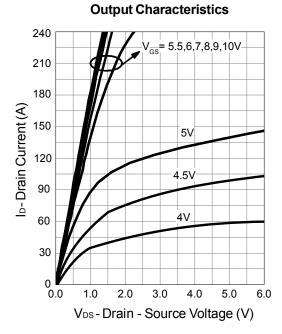
# **Electrical Characteristics** $(T_c = 25^{\circ}C \text{ Unless Otherwise Noted})$

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
Static Cha	aracteristics	•					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA		80	-	-	V
I <sub>DSS</sub>	Zana Cata Valta na Busin Comunit	$V_{DS}$ =80V, $V_{GS}$ =0V		-	-	1	
	Zero Gate Voltage Drain Current		T <sub>J</sub> =85°C	-	-	10	μΑ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=25$	0μΑ	2.0	3.0	4.0	V
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$		-	-	±100	nA
R <sub>DS(ON)</sub> *	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =70A		-	4.8	6.0	mΩ
Diode Cha	aracteristics	•			•	•	
V <sub>SD</sub> *	Diode Forward Voltage	I <sub>SD</sub> =70 A, V <sub>GS</sub> =0V		-	0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	-I <sub>SD</sub> =70 A, dI <sub>SD</sub> /dt=100A/μs		-	30	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge			-	52	-	nC
Dynamic (	Characteristics				•		
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz		-	1.6	-	Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, Frequency=1.0MHz		-	4687	-	pF
C <sub>oss</sub>	Output Capacitance			-	665	-	
C <sub>rss</sub>	Reverse Transfer Capacitance			-	235	-	
t <sub>d(ON)</sub>	Turn-on Delay Time	$V_{DD}$ =40V, $R_{G}$ =6 $\Omega$ , $I_{DS}$ =70A, $V_{GS}$ =10V,		-	26	-	ns
T <sub>r</sub>	Turn-on Rise Time			-	17	-	
t <sub>d(OFF)</sub>	Turn-off Delay Time			-	41	-	
T <sub>f</sub>	Turn-off Fall Time			-	53	-	
Gate Chai	ge Characteristics	•					
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =64V, V <sub>GS</sub> =10V, I <sub>DS</sub> =70A		-	115	-	nC
$Q_{gs}$	Gate-Source Charge			-	15	-	
$Q_{gd}$	Gate-Drain Charge			-	44	-	

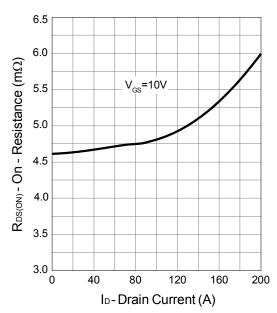
Note \* : Pulse test ; pulse width  $\leq$ 300 $\mu$ s, duty cycle  $\leq$ 2%.



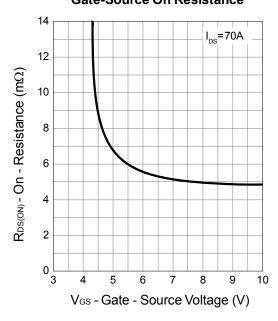
## **Typical Operating Characteristics**



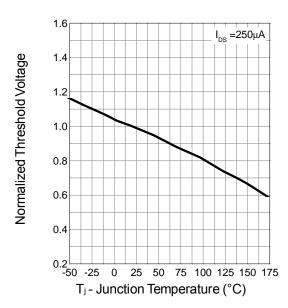
#### **Drain-Source On Resistance**



### **Gate-Source On Resistance**



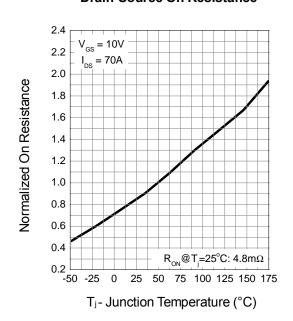
#### **Gate Threshold Voltage**



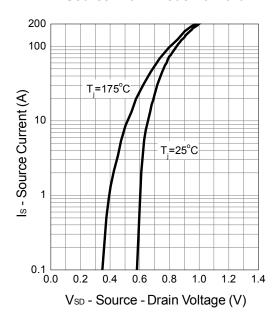


## **Typical Operating Characteristics (Cont.)**

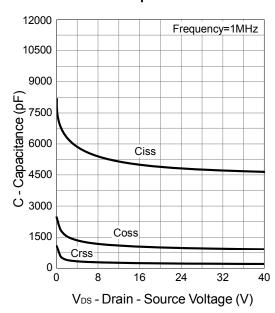
## Drain-Source On Resistance



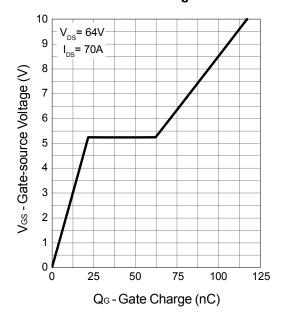
#### **Source-Drain Diode Forward**



#### Capacitance

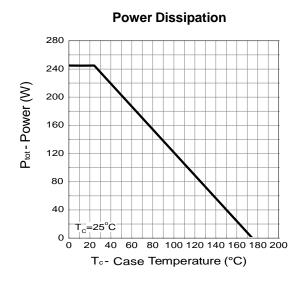


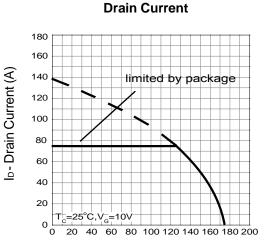
#### **Gate Charge**





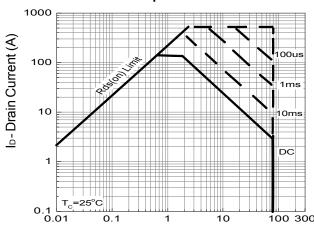
## **Typical Operating Characteristics (Cont.)**





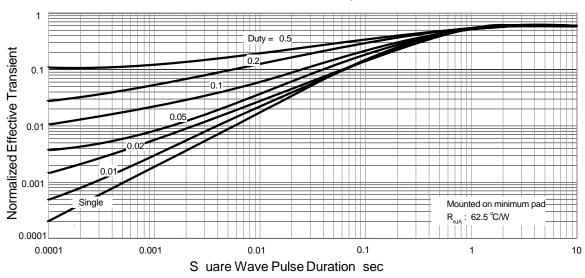
T<sub>c</sub>-Case Temperature (°C)

#### **Safe Operation Area**



V<sub>DS</sub> - Drain - Source Voltage (V)

#### **Thermal Transient Impedance**





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